ECE 695 : Reliability Physics of Nano-Transistors
Lecture 14B: Voltage dependent HCI

Muhammad Ashraful Alam
alam@purdue.edu
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Substrate vs. gate current

\[
\begin{align*}
\log\left(\frac{I_G}{I_D}\right) &= \frac{\Phi_e}{q\bar{E}_m\lambda_e} + c, \\
\log\left(\frac{I_{sub}}{I_D}\right) &= \frac{\Phi_i}{q\bar{E}_m\lambda_e} + b
\end{align*}
\]

\[
\log\left(\frac{I_g}{I_d}\right) = 4 \times 10^{-4}\left(\frac{I_{sub}}{I_d}\right)^{\psi_i/\psi_i}
\]

\[
\frac{I_G}{I_D} = \left[\frac{\Phi_i}{e^{qE_m\lambda_e}}\right] \frac{\Phi_e}{\Phi_i} = \left[\frac{I_{sub}}{I_D}\right] \frac{\Phi_e}{\Phi_i}
\]


Voltage Scaling by Substrate Current

\[ \log\left( \frac{I_G}{I_D} \right) = \frac{\Phi_e}{qE_m\lambda_e} + c. \]

\[
\log\left( \frac{I_{\text{sub}}}{I_D} \right) = \frac{\Phi_i}{qE_m\lambda_e} + b
\]

\[ t_0(V_G, V_D) = \frac{A}{I_G} = \frac{A}{I_D} \left[ \frac{I_D}{I_{\text{sub}}} \right] \frac{\Phi_e}{\Phi_i} \]

\[ t_0(V_G, V_D) = \frac{A}{I_G} = \frac{A}{I_D} \frac{\nu_{\text{sat}}}{e^{-B/(V_D-V_{D,sat})}} \]

I_{sub}/V_D Correlation

\[
\frac{I_G}{I_D} = e^{\frac{-\Phi_i}{qE_m\lambda_e}} = \left[ \frac{I_{sub}}{I_D} \right]^{\frac{\Phi_e}{\Phi_i}}
\]

\[
t_0(V_G, V_D) = \frac{A}{I_G} = \frac{A}{I_D} \left[ \frac{I_D}{I_{sub}} \right]^{\frac{\Phi_e}{\Phi_i}}
\]

\[
t_0(V_G, V_D) = \frac{A}{I_G} = \frac{A}{I_D} \frac{\nu_{sat}}{e^{-B/(V_D-V_{D,\text{sat}})}}
\]

\[
\Rightarrow \left[ \frac{I_D}{I_{sub}} \right]^{\frac{\Phi_e}{\Phi_i}} = \frac{\nu_{sat}}{e^{-B/(V_D-V_{D,\text{sat}})}}
\]
Outline

1. Background and empirical scaling
2. Theory of hot carriers: Hydrodynamic model
3. Theory of hot carriers: Monte Carlo model
4. Theory of hot carriers: Universal Scaling
5. Conclusion
6. Appendices
**V- dependence at low-voltages:**

Monte Carlo

\[ V(x) = V_{dsat} + A e^{x/l} \]

- Pinched-off region
- Impact-ionization
- Hot-electrons \((T_e)\)
- Scattering

(see Prof. Lundstrom’s EE656 Notes at Nanohub)
What is the problem?

Classical MOSFET

\[ n(E) \sim e^{-E/kT_e} \]

Modern MOFET

\[ n(E) \sim e^{-E/kT_e} \]

Knee voltage \( \sim V_D \)

\[ t_0^{-1}(V_G, V_D) = I_G \propto \frac{I_D}{I_{\text{sub}}} \left[ \frac{I_{\text{sub}}}{I_D} \right]^{\Phi_e/\Phi_i} \]

\[ t_0^{-1}(V_G, V_D) = I_G = \frac{r_{ii} m I_D}{k_1 W} + \frac{r_{ii}^2 m I_D^2}{k_2 W^2} + \frac{V_d \gamma I_D^\alpha}{k_3 W^\alpha} \]
HCl by Monte Carlo Simulation

Conduction band …

Valence band …

Density of states …

Carrier distribution …

@ low field…

@ medium field…

@ high field…

Energy [eV]

DOS [10^{22} cm^{-3} eV^{-1}]

E = 0.5 eV

1 kV/cm Si <100>

100 kV/cm

300kV/cm

2002 School on Computational Material Science

May 21-31, 2002
Monte Carlo Simulation in a MOSFET

Also see:

\[ k(t) = k_0 - \int_0^t \frac{qE(x(t'))}{\hbar} dt' \]

\[ x(t) = x_0 + \int_0^t \nu(x(t')) dt \]

Why is the electron off-center?
Is the notion of threshold energy clear?

MC on nanohub
bulkmc (Arizona)
demons (Purdue)
SMC (Bell Labs)
Device/Monte-Carlo Simulation

Simulated with special Monte Carlo Simulator from Bell Labs.

Hot carrier distribution can be calculated accurately from Monte Carlo simulation. It is a very difficult calculation however.
$N_{IT}$ correlation with hot holes

Monte Carlo simulation

Damage primarily due to broken Si-O bonds

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Recall: Voltage Dependent Constant $t_0$

$$N_{SiH}^{IT} = \left( \frac{k_F(V_G, V_D)N_0}{k_R} \right)^n t^n \equiv \left( \frac{t}{t_0} \right)^n = f_1 \left( \frac{t}{t_0} \right)$$

$$N_{SiO}^{IT} = \sum_E g(E) \left[ 1 + e^{-k_F(V_G, V_D)t} \right] dE \equiv f_2 \left( \frac{t}{t_0} \right)$$

$$t_0^{-1}(V_G, V_D) = I_G = k \frac{I_D}{W_{eff}} \left[ \frac{I_{sub}}{I_D} \right] \Phi_e/\Phi_i$$

How to determine $t_0$ ...

$$t^*/t_0(V_G, V_D) = f^{-1}(N_{it}^*) = \text{const.}$$

$$t_0(V_G, V_D) \propto t^*(V_G, V_D)$$

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Universality of Degradation (NMOS)

Varghese, IRPS, 2008.

\[ T_0 = 27^\circ C \]

\[
\frac{1}{S} \sim V_D^{-38.7}
\]

\[
\frac{1}{h} \sim V_D^{-39}
\]

\( \Delta \text{CP (a. u.)} \)

Time (s)

10^0 10^2 10^4 10^6 10^8 10^{10}

5.5V 6.0V 6.5V 7.0V

B-D Model

Line: Universal curve
Symbols: Measurements

5.5V

6.0V

6.5V

7.0V

10^0 10^2 10^4 10^6 10^8 10^{10}

\( \Delta \text{CP (a. u.)} \)

Time (s)

\[ T_1 : T_2 : T_3 = \frac{1}{S_1} : \frac{1}{S_2} : \frac{1}{S_3} \]
DePMOS show sign reversal in $\Delta I_{DLIN}$, reflecting change from acceptor-like to donor-like traps.
Discussion: Voltage Acceleration

Voltage acceleration factor reduces at higher gate biases

Voltage dependence of hot carrier profile from Monte Carlo simulation is required to understand the trends in acceleration factors
Conclusions

- Theory of HCI has been developed over many years – first by C. Hu via Hydrodynamic solution of BTE and later by Hess/Bude via Monte Carlo solution of BTE. Both provide reasonable explanation of voltage acceleration factors for HCI degradation for relatively long channel transistors. And both demonstrate universal scaling.

- For shorter channel transistors at low voltages, solution of BTE is difficult (MC has too few yield, while hydrodynamic model is inappropriate). Varghese’s Universal scaling theory provides an excellent alternative.
Review Questions

1. Why is $I_{sub}$ called a thermometer of hot electron distribution? Why can you not simply measure hot electrons by looking at the drain current?

2. What are the three methods of HCI voltage acceleration?

3. If theory of universal scaling is so good, why not use it all the time? (Hint: Think about measurement time)

4. How many devices and how long do you need for HCI testing based on hydrodynamic theory? What about Universal scaling theory? What about direct lifetime projection?

5. If Monte Carlo simulation is so good, why does not everyone use Monte Carlo simulator to do lifetime testing?

6. We assumed $t_0 \sim 1/IG \sim 1/kF$, what theory of SiH bond dissociation did we use?

7. Explain the origin of power-exponent of 2 in the Keldysh theory.

8. What is the impact ionization threshold for GaAs?


The theory of Impact ionization and Keldysh formulation are discussed in many textbooks, see for example, K. Hess book on semiconductor devices, Chapter 13. Or, Ridley’s book on Quantum Processes, p. 27 . Also, see C. Jungemann, SSE 39(7), p. 1079, 1996)